

# SSCP005GS3

### High Frequency High Gain PNP Power BJT

Features

| VCE  | VBE | VCESAT Typ. | IC  |  |
|------|-----|-------------|-----|--|
| -40V | -6V | -150mV      | -3A |  |

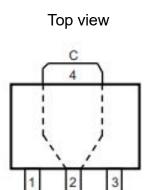
### > Description

This device is produced with advanced high carrier density technology, which is especially used to minimize saturation voltage drop. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package. Excellent thermal and electrical capabilities.

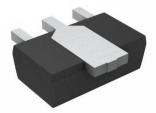
#### > Applications

- Battery powered circuits
- Low in-line power dissipation circuits
- Power regulator

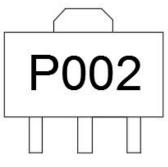
Pin configuration



SOT89-3L



Bottom view



Marking

### > Ordering Information

| Device     | Package | Shipping  |
|------------|---------|-----------|
| SSCP005GS3 | SOT89   | 1000/Reel |



## > Absolute Maximum Ratings(T<sub>A</sub>=25°C unless otherwise specified)

| Symbol           | Parameter                                  | Ratings    | Unit |  |
|------------------|--|------------|------|--|
| V <sub>сво</sub> | o Collector-Base Voltage                   |            | V    |  |
| V <sub>CEO</sub> | V <sub>CEO</sub> Collector-Emitter Voltage |            | V    |  |
| V <sub>EBO</sub> | Emitter-Base Voltage                       | -6         | V    |  |
| I                | Collector Current@Note1                    | -3         | А    |  |
| lc               | Collector Current@Note2                    | -2         |      |  |
| Ісм              | Pulsed Collector Current@Note3             | -6         | A    |  |
| PD               | Power Dissipation@Note1                    | 3.0        |      |  |
| ΓD               | Power Dissipation@Note2                    | 1.5        | W    |  |
| T <sub>A</sub>   | Operation Temperature Range                | -40 to 85  | °C   |  |
| TL               | TL Lead Temperature                        |            | °C   |  |
| $T_{J},T_{STG}$  | Operation and Storage temperature range    | -55 to 150 | °C   |  |

# > Thermal Resistance Ratings

| Symbol           | Symbol Parameter            |    | Unit |
|------------------|-----------------------------|----|------|
| Р                | Junction-to-Ambient Thermal | 10 |      |
| R <sub>0JA</sub> | Resistance@Note1            | 49 | °C/W |
|                  | Junction-to-Ambient Thermal | 00 |      |
| R <sub>θJA</sub> | Resistance@Note2            | 89 |      |



# $\succ$ Electronics Characteristics(T<sub>A</sub>=25°C unless otherwise specified)

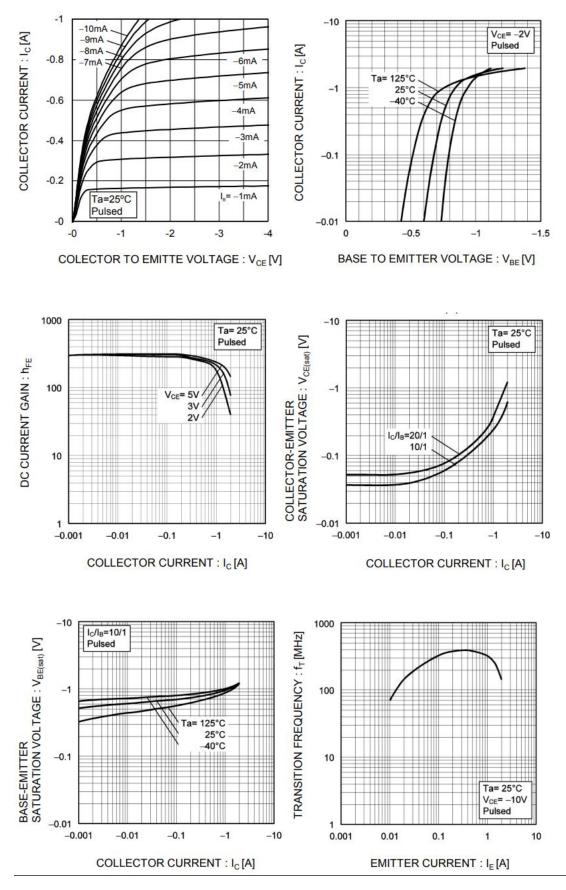
| Symbol | bol Parameter Test Conditions |                   | Min | Тур.     | Мах  | Unit |
|--------|-------------------------------|-------------------|-----|----------|------|------|
| BVCBO  | Collector-Base                | IC=-50uA          | -40 |          |      | V    |
| вусво  | Breakdown Voltage             | IE=0              | -40 |          |      | V    |
| BVCEO  | Collector-Emitter             | IC=-1mA           | -40 |          |      | V    |
| BVCEO  | Breakdown Voltage             | IB=0              | -40 |          |      | v    |
|        | Emitter-Base                  | IE=-1uA           | -6  | <u> </u> |      | V    |
| BVEBO  | Breakdown Voltage             | IC=0              | -0  |          |      | V    |
| ІСВО   | Collector cut off             | VCB=-20V          |     |          | -0.1 | uA   |
| ЮВО    | current                       | IE=0              |     |          |      |      |
|        | Emitter cut off               | VEB=-4V           |     |          | 0.4  |      |
| IEBO   | current                       | IC=0              |     |          | -0.1 | uA   |
| HFE    | DC Current                    | VCE=-2V           | 100 | 200      | 350  |      |
| HFE    | Gain@Note3                    | IC=-0.5A          | 100 | 200      | 350  |      |
| VOEDAT | Collector-Emitter             | IC=-1.5A          |     |          | 0.0  |      |
| VCESAT | Saturation Voltage            | IB=-80mA          |     | -0       | -0.2 | V    |
| VBESAT | Base-Emitter                  | IC=-1.5A          |     |          | -1.2 | V    |
| VDESAI | Saturation Voltage            | IB=-80mA          |     | -1.2     | V    |      |
| £      | Tropolition from the second   | VCE=-5V, IE=-0.1A | 50  | 80       |      |      |
| fT     | Transition frequency          | f=10MHz           | 50  |          |      | MHz  |

#### Notes:

- 1. Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper.
- 2. Surface mounted on FR-4 Board using minimum pad size, 1oz copper.
- 3. Pulse width=300us, Duty Cycle<2%.



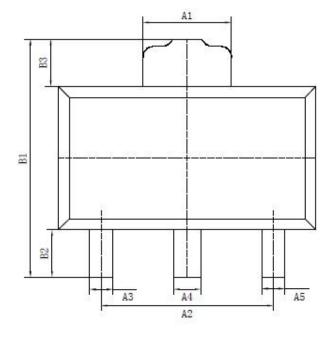
## > Typical Performance Characteristics

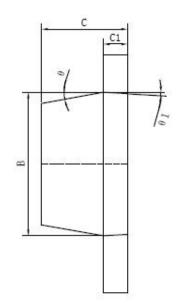


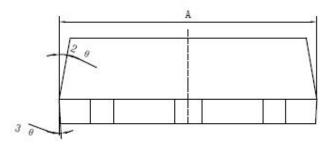


# SSCP005GS3

## > Package Information







| <b></b> 尽寸 | 最小(mm) | 最大(mm) | 标注 尺寸 | 最小(mm)             | 最大(mm) |
|------------|--------|--------|-------|--------------------|--------|
| A          | 4.40   | 4.60   | B3    | 0.82               | 0.83   |
| A1         | 1.65   | 1.75   | С     | 1.40               | 1.60   |
| A2         | 2.95   | 3.05   | C1    | 0.35               | 0.45   |
| A3         | 0.35   | 0.45   | θ     | 6° TYP4            |        |
| A4         | 0.43   | 0.53   | θ1    | 3° TYP4<br>6° TYP4 |        |
| A5         | 0.35   | 0.45   | θ2    |                    |        |
| В          | 2.40   | 2.60   | θ 3   | 3° TYP4            |        |
| B1         | 4.05   | 4.25   |       |                    |        |
| B2         | 0.82   | 0.83   |       |                    |        |



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